

Product Summary

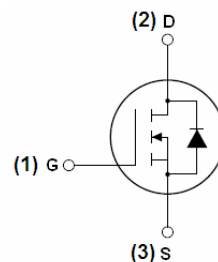
Part #	V_{DS}	$R_{DS(on).typ}$ (@ $V_{GS}=10V$)	$R_{DS(on).typ}$ (@ $V_{GS}=4.5V$)	I_D
EFM850N10D	100	85m Ω	100m Ω	15A

Description

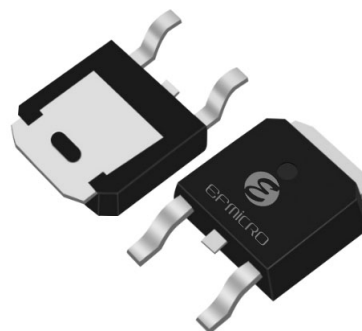
- The EFM850N10D is the high cell density trench
- N-ch MOSFETs which provide excellent
- RDSON and gate charge for most of the
- synchronous buck converter applications.
- The EFM850N10D meet the RoHS and Green
- Product requirement, 100 % EAS guaranteed
- with full function reliability approved.

Application

- Super Low Gate Charge 100% EAS Guaranteed
- Green Device Available Excellent CdV/dt effect decline
- Advanced high cell density Trench technology



N-Channel MOSFET



TO-252-2L

Ordering Information:

Part NO.	EFM850N10D
Marking	850N10D****
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

Absolute Maximum Ratings ($T_C=25^{\circ}C$)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	15	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	60	A
Maximum Power Dissipation	P_D	50	W
Single pulse avalanche energy ^(Note 5)	E_{AS}	200	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JC}$	3	$^{\circ}C/W$
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• Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)

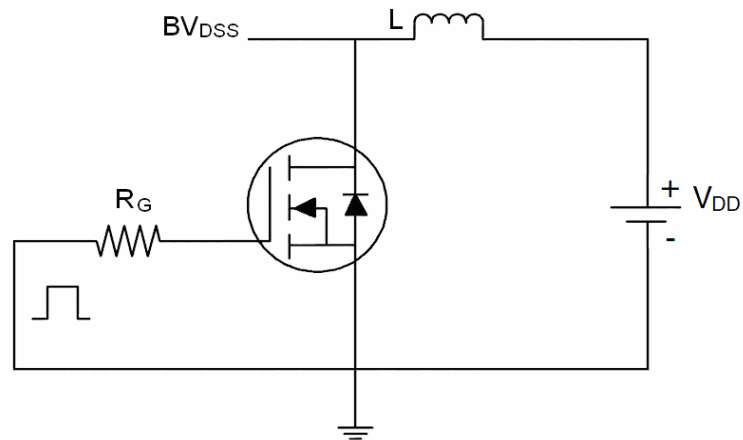
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250uA	100	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V V _{GS} =0V	--	--	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V V _{DS} =0V	--	--	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =250uA	1.0	1.6	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V I _D =10A	--	85	95	mΩ
		V _{GS} =4.5V I _D =10A	--	100	110	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V I _D =10A	--	10	--	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{ISS}	V _{DS} =50V V _{GS} =0V F=1.0MHz	--	1535	--	PF
Output Capacitance	C _{OSS}		--	60	--	PF
Reverse Transfer Capacitance	C _{RSS}		--	30	--	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, R _L =6. 4Ω V _{GS} =10V R _G =3 Ω,	--	15	--	nS
Turn-on Rise Time	t _r		--	5	--	nS
Turn-Off Delay Time	t _{d(off)}		--	25	--	nS
Turn-Off Fall Time	t _f		--	7	--	nS
Total Gate Charge	Q _g	V _{DS} =50V I _D =10A V _{GS} =10V	--	22.3	--	nC
Gate-Source Charge	Q _{gs}		--	2.87	--	nC
Gate-Drain Charge	Q _{gd}		--	6.14	--	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V I _S =15A	--	--	1.2	V
Diode Forward Current ^(Note 2)	I _S		--	--	15	A

Notes:

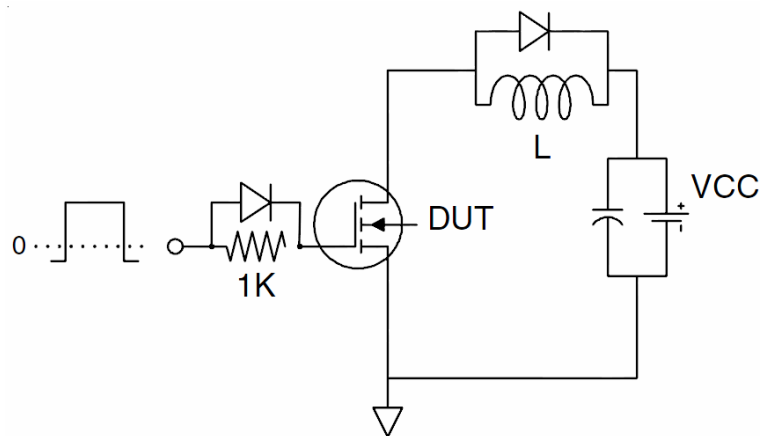
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T_J=25°C, V_{DD}=50V, V_G=10V, L=0.5mH, R_G=25Ω

• Test Circuit

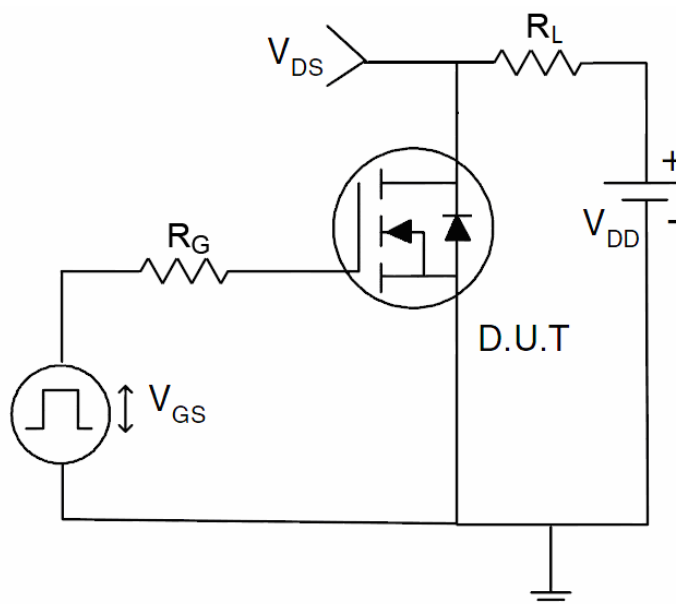
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



• Typical Characteristics

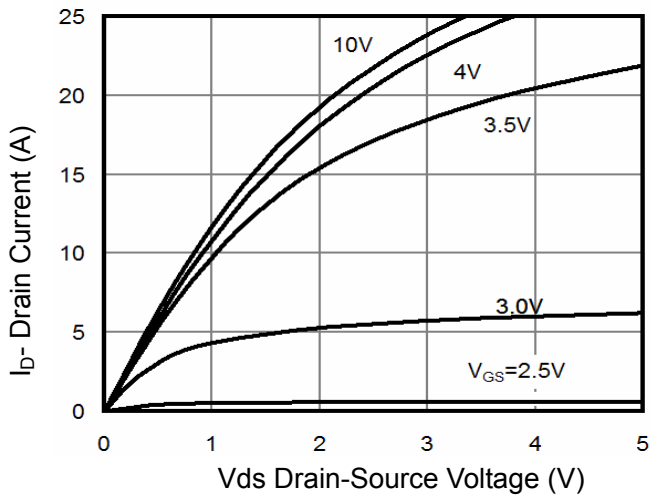


Figure 1 Output Characteristics

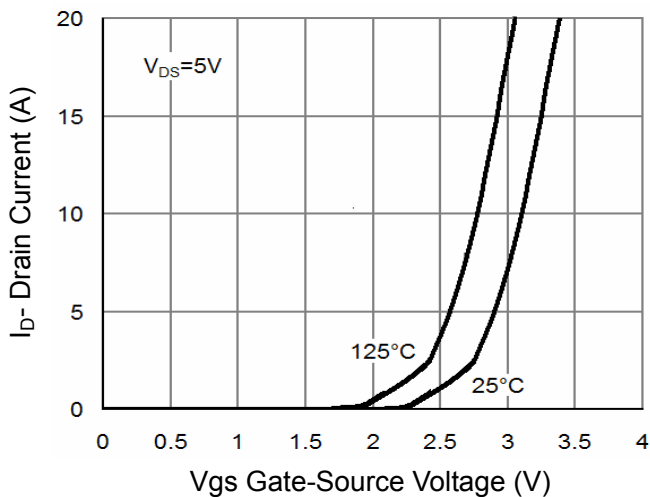


Figure 2 Transfer Characteristics

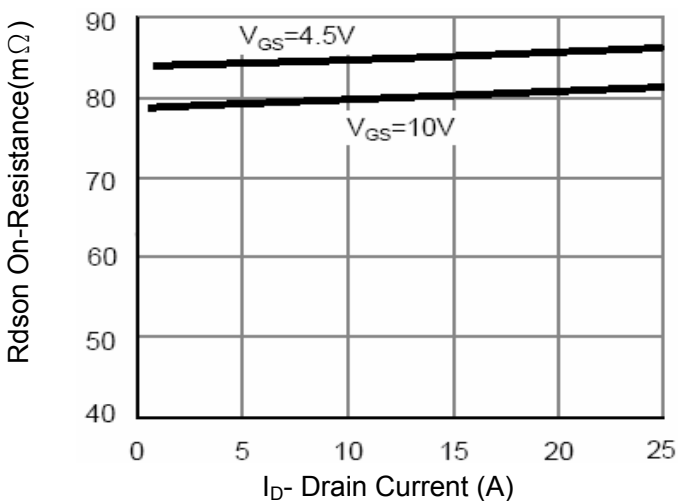


Figure 3 Rdson- Drain Current

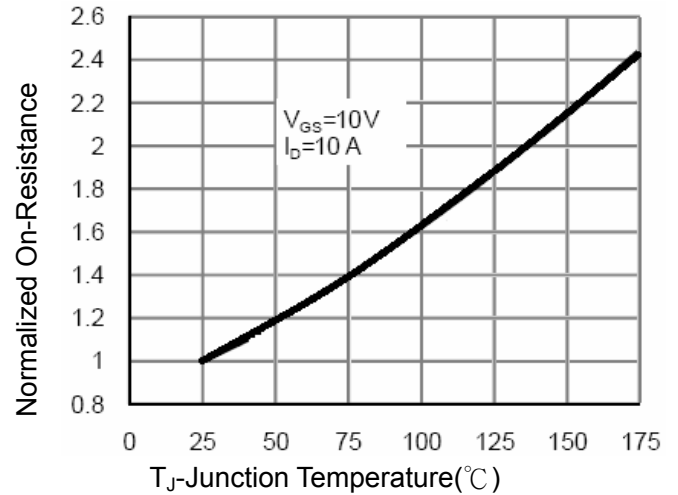


Figure 4 Rdson-Junction Temperature

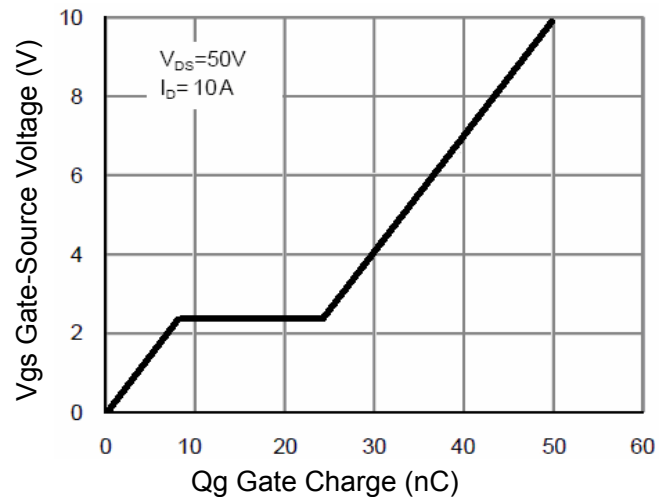


Figure 5 Gate Charge

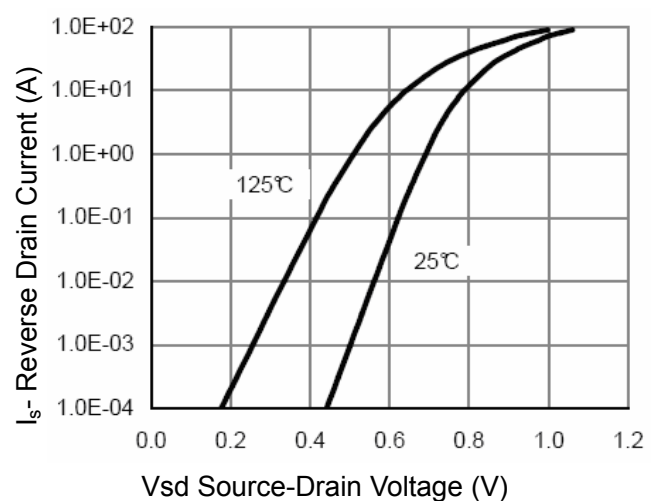


Figure 6 Source- Drain Diode Forward

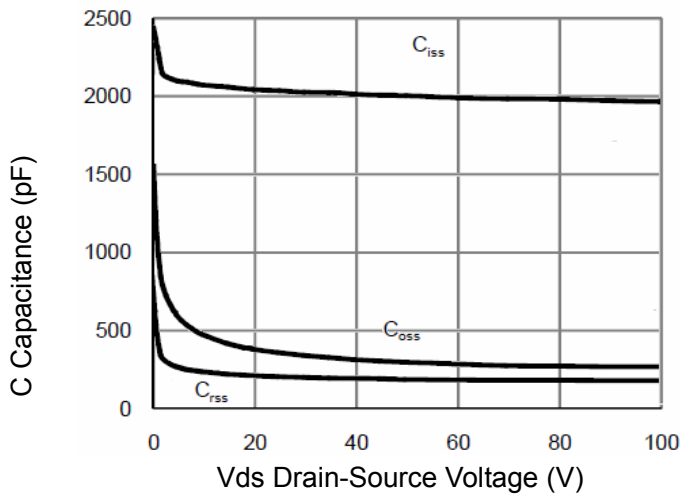


Figure 7 Capacitance vs Vds

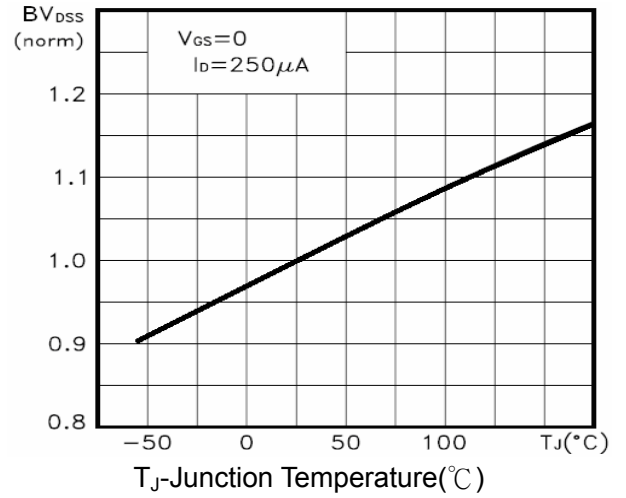


Figure 9 BV_{DSS} vs Junction Temperature

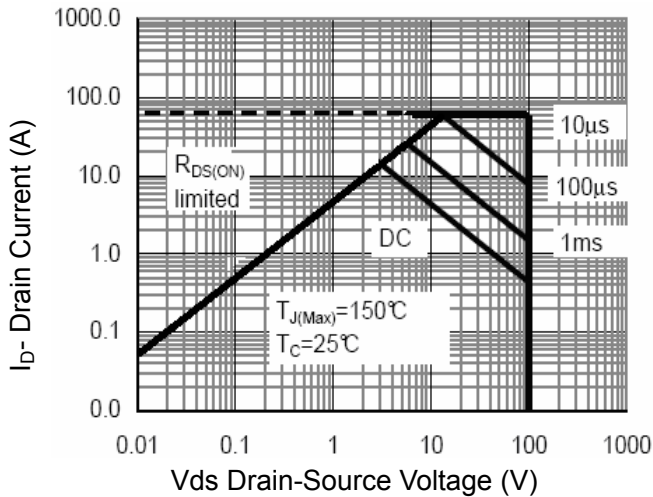


Figure 8 Safe Operation Area

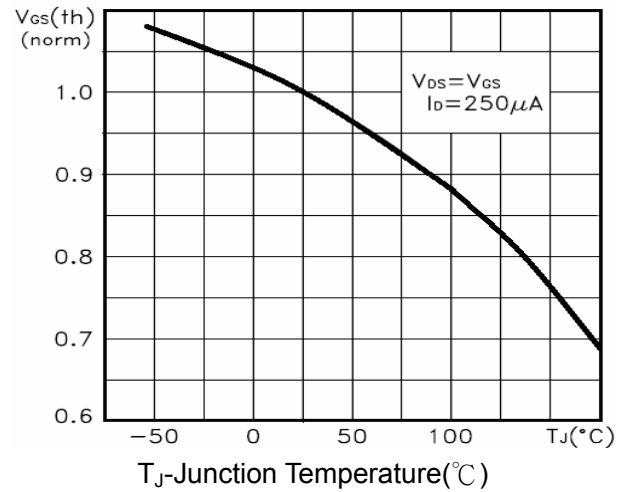


Figure 10 $V_{GS(th)}$ vs Junction Temperature

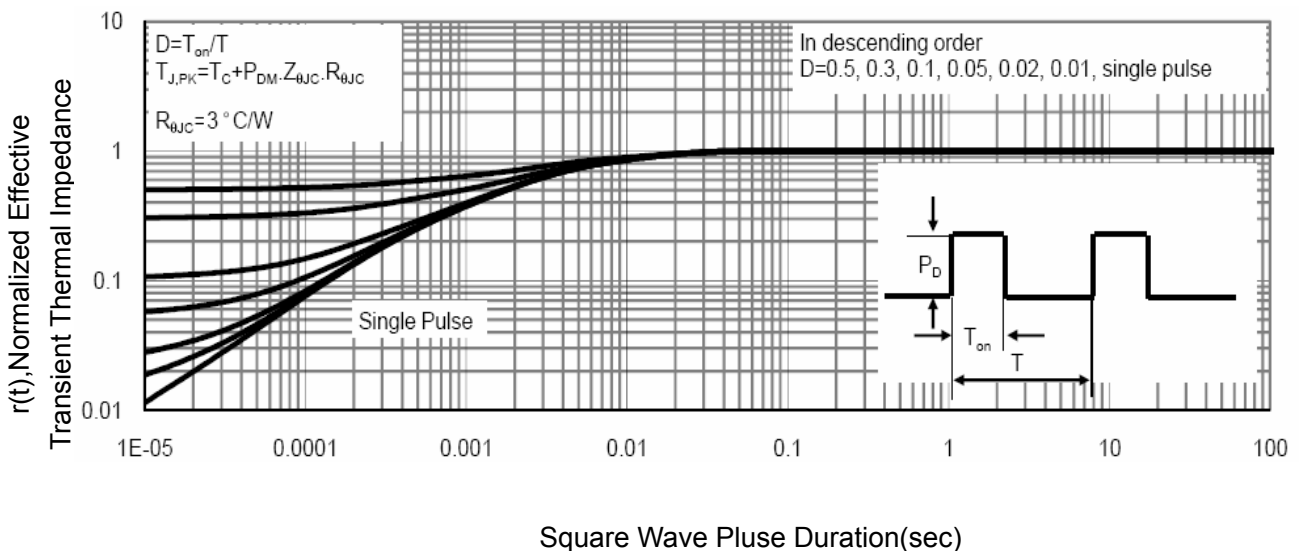
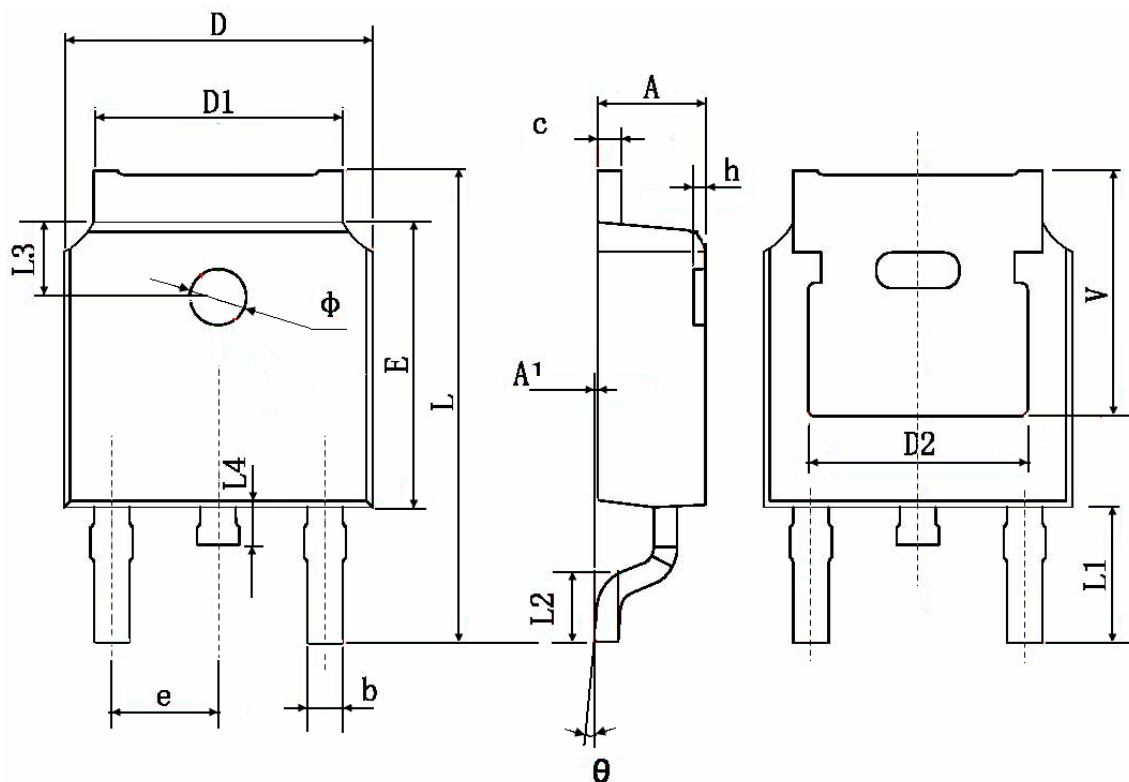


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.83 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	